

Specifications HGTP10N40C1D, HGTP10N40E1D, HGTP10N50C1D, HGTP10N50E1D

Electrical Specifications $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

PARAMETERS	SYMBOL	TEST CONDITIONS	LIMITS				UNITS	
			HGTP10N40C1D, HGTP10N40E1D		HGTP10N50C1D, HGTP10N50E1D			
			MIN	MAX	MIN	MAX		
Collector-Emitter Breakdown Voltage	BV_{CES}	$I_C = 1\text{mA}, V_{GE} = 0$	400	-	500	-	V	
Gate Threshold Voltage	$V_{GE(TH)}$	$V_{GE} = V_{CE}, I_C = 1\text{mA}$	2.0	4.5	2.0	4.5	V	
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 400\text{V}, T_C = +25^\circ\text{C}$	-	250	-	-	μA	
		$V_{CE} = 500\text{V}, T_C = +25^\circ\text{C}$	-	-	-	250	μA	
		$V_{CE} = 400\text{V}, T_C = +125^\circ\text{C}$	-	1000	-	-	μA	
		$V_{CE} = 500\text{V}, T_C = +125^\circ\text{C}$	-	-	-	1000	μA	
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 20\text{V}, V_{CE} = 0$	-	100	-	100	nA	
Collector-Emitter On Voltage	$V_{CE(ON)}$	$I_C = 10\text{A}, V_{GE} = 10\text{V}$	-	2.5	-	2.5	V	
		$I_C = 17.5\text{A}, V_{GE} = 20\text{V}$	-	3.2	-	3.2	V	
Gate-Emitter Plateau Voltage	V_{GEP}	$I_C = 5\text{A}, V_{CE} = 10\text{V}$	-	6 (typ)	-	6 (typ)	V	
On-State Gate Charge	$Q_{G(ON)}$	$I_C = 5\text{A}, V_{CE} = 10\text{V}$	-	19 (typ)	-	19 (typ)	nC	
Turn-On Delay Time	$t_{D(ON)}$	$I_C = 10\text{A}, V_{CE(CLIP)} = 300\text{V},$ $L = 50\mu\text{H}, T_J = +100^\circ\text{C},$ $V_{GE} = 10\text{V}, R_G = 50\Omega$	-	50	-	50	ns	
Rise Time	t_{RI}		-	50	-	50	ns	
Turn-Off Delay Time	$t_{D(OFF)}$		-	400	-	400	ns	
Fall Time	t_{FI}		40E1D, 50E1D	680 (typ)	1000	680 (typ)	1000	ns
			40C1D, 50C1D	400 (typ)	500	400 (typ)	500	ns
Turn-Off Energy Loss per Cycle (Off Switching Dissipation = $W_{OFF} \times \text{Frequency}$)	W_{OFF}	$I_C = 10\text{A}, V_{CE(CLIP)} = 300\text{V},$ $L = 50\mu\text{H}, T_J = +100^\circ\text{C},$ $V_{GE} = 10\text{V}, R_G = 50\Omega$	1810 (typ)				μJ	
			1070 (typ)				μJ	
Thermal Resistance Junction-to-Case	$R_{\theta JC}$		-	1.67	-	1.67	$^\circ\text{C/W}$	
Diode Forward Voltage	V_{EC}	$I_{EC} = 10\text{A}$	-	2	-	2	V	
Diode Reverse Recovery Time	t_{RR}	$I_{EC} = 10\text{A}, dI/dt = 100\text{A}/\mu\text{s}$	-	100	-	100	ns	

Typical Performance Curves

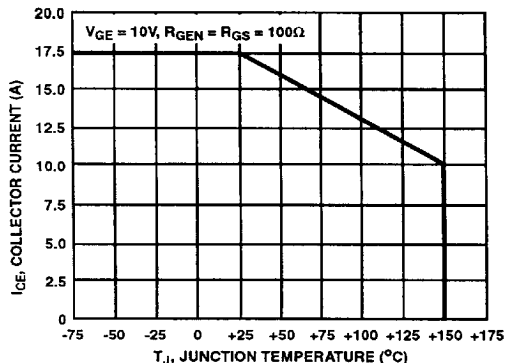


FIGURE 1. MAX. SWITCHING CURRENT LEVEL. R_G = 50Ω, V_{GE} = 0V ARE THE MIN. ALLOWABLE VALUES

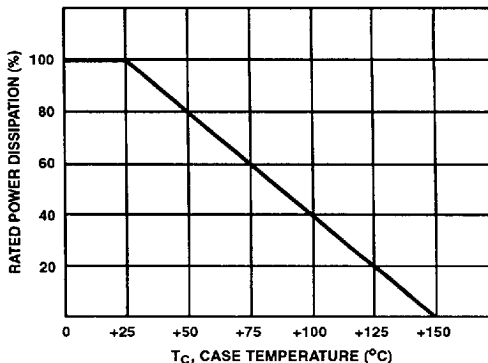


FIGURE 2. POWER DISSIPATION vs TEMPERATURE DERATING CURVE

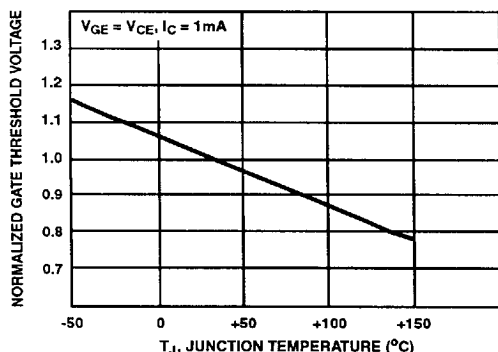


FIGURE 3. TYPICAL NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

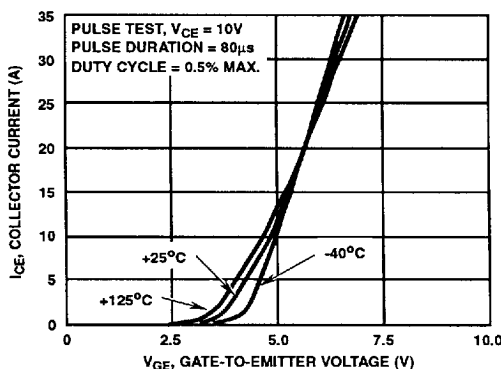


FIGURE 4. TYPICAL TRANSFER CHARACTERISTICS

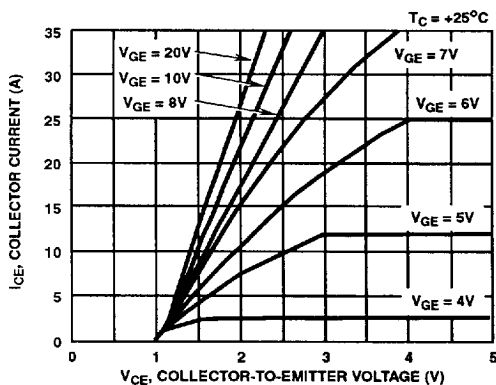


FIGURE 5. TYPICAL SATURATION CHARACTERISTICS

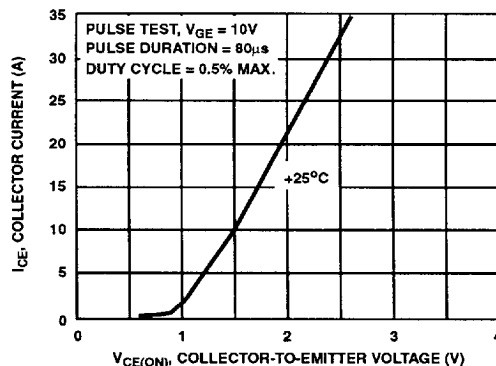


FIGURE 6. TYPICAL COLLECTOR-TO-EMITTER ON-VOLTAGE vs COLLECTOR CURRENT

IGBTs

HGTP10N40C1D, HGTP10N40E1D, HGTP10N50C1D, HGTP10N50E1D

Typical Performance Curves (Continued)

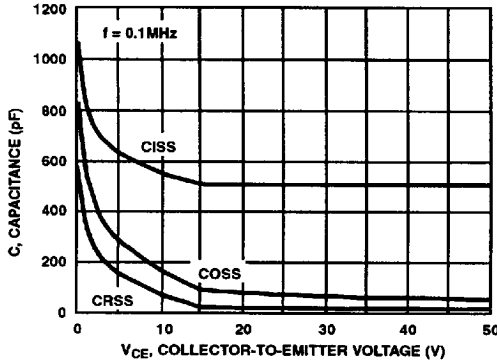


FIGURE 7. CAPACITANCE vs COLLECTOR-TO-EMITTER VOLTAGE

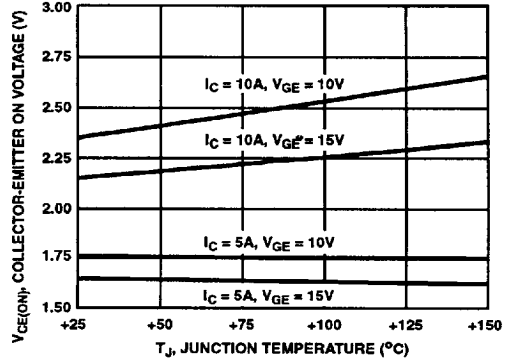


FIGURE 8. TYPICAL $V_{CE(ON)}$ vs TEMPERATURE

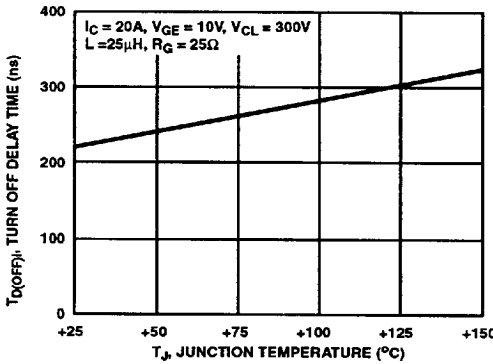


FIGURE 9. TYPICAL TURN-OFF DELAY TIME

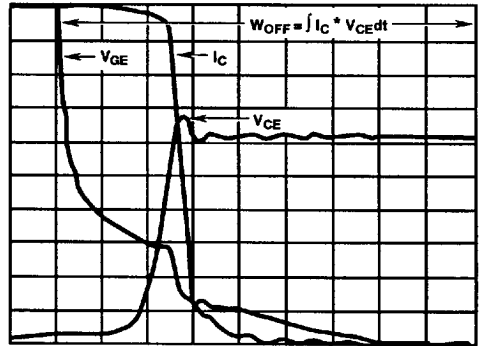


FIGURE 10. TYPICAL INDUCTIVE SWITCHING WAVEFORMS

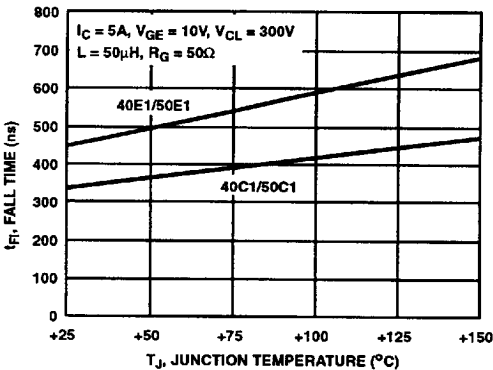


FIGURE 11. TYPICAL FALL TIME ($I_C = 5A$)

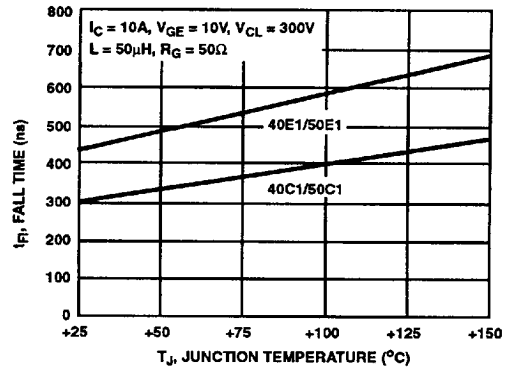


FIGURE 12. TYPICAL FALL TIME ($I_C = 10A$)

HGTP10N40C1D, HGTP10N40E1D, HGTP10N50C1D, HGTP10N50E1D

Typical Performance Curves (Continued)

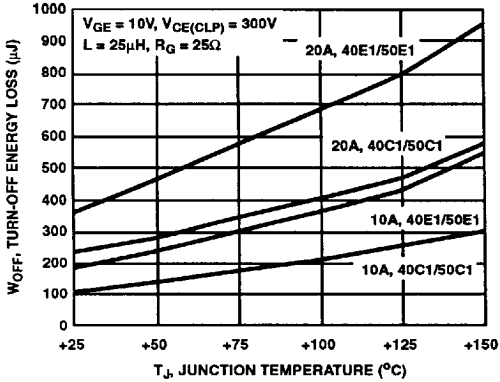


FIGURE 13. TYPICAL CLAMPED INDUCTIVE TURN-OFF SWITCHING LOSS/CYCLE

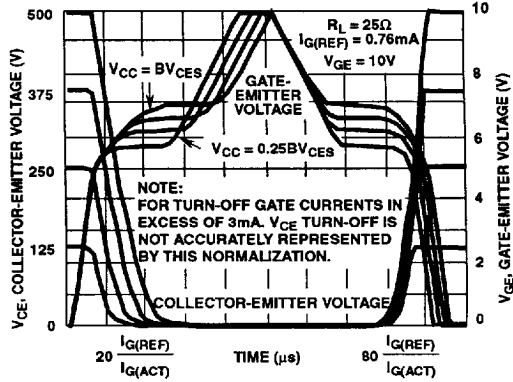


FIGURE 14. NORMALIZED SWITCHING WAVEFORMS AT CONSTANT GATE CURRENT. (REFER TO APPLICATION NOTES AN7254 AND AN7260)

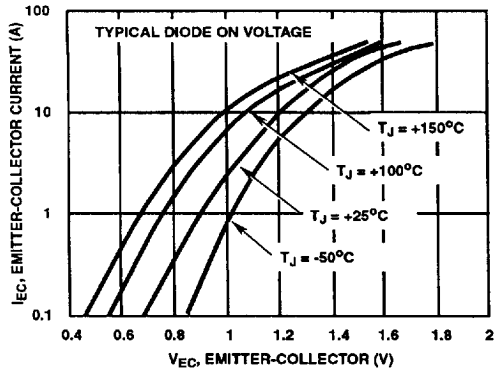


FIGURE 15. TYPICAL DIODE EMITTER-TO-COLLECTOR VOLTAGE vs CURRENT FOR ALL TYPES

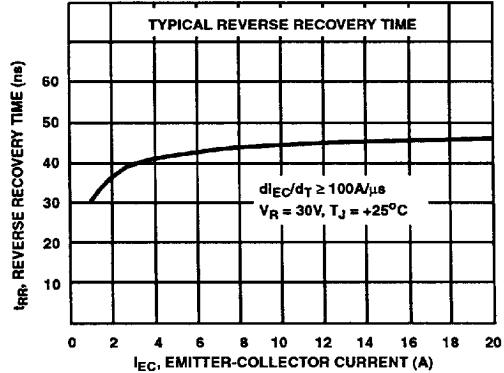


FIGURE 16. TYPICAL DIODE REVERSE-RECOVERY TIME FOR ALL TYPES

IGBTs

Test Circuit

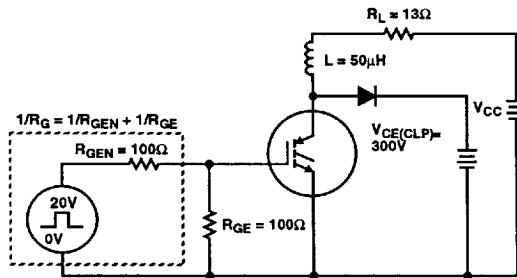


FIGURE 17. INDUCTIVE SWITCHING TEST CIRCUIT